

2PB709ART 45 V, 100 mA PNP general-purpose transistor Rev. 01 — 19 March 2007

Product data sheet

1. Product profile

1.1 General description

PNP general-purpose transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: 2PD601ART.

1.2 Features

- General-purpose transistor
- Small SMD plastic package

1.3 Applications

General-purpose switching and amplification

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-45	V
I _C	collector current		-	-	-100	mA
h _{FE}	DC current gain	$V_{CE} = -10 \text{ V};$ $I_{C} = -2 \text{ mA}$	210	-	340	

2. Pinning information

	Simplified outline	Symbol
base		
emitter		3
collector		
	emitter	emitter



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3. Ordering information

Table 3. Order	Ordering information						
Type number	Package						
	Name	Description	Version				
2PB709ART	-	plastic surface-mounted package; 3 leads	SOT23				

4. Marking

Table 4. Markir	ng codes	
Type number	Marking code ^[1]	
2PB709ART	C5*	

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

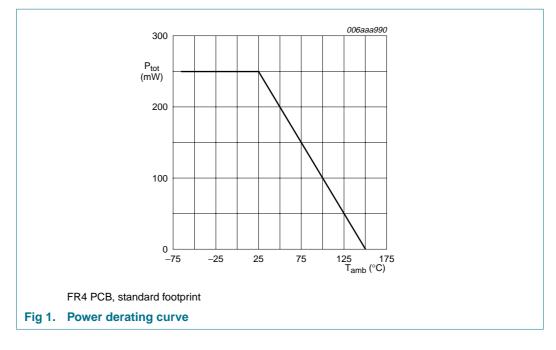
Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0 9 (,		
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	-45	V
V_{CEO}	collector-emitter voltage	open base	-	-45	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current		-	-100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-200	mA
I _{BM}	peak base current	single pulse; $t_p \leq 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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6. Thermal characteristics

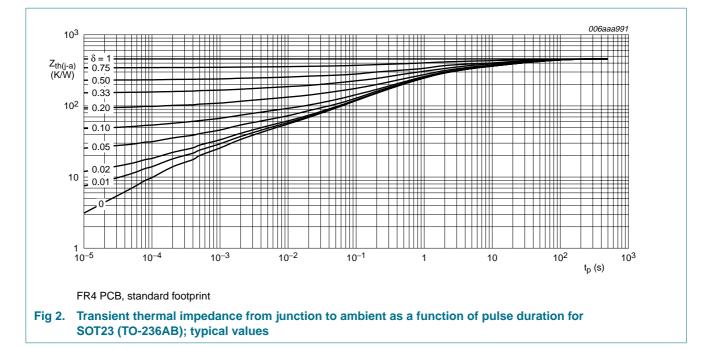
Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	140	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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7. Characteristics

Table 7.Characteristics

 $T_{amb} = 25 \circ C$ unless otherwise specified.

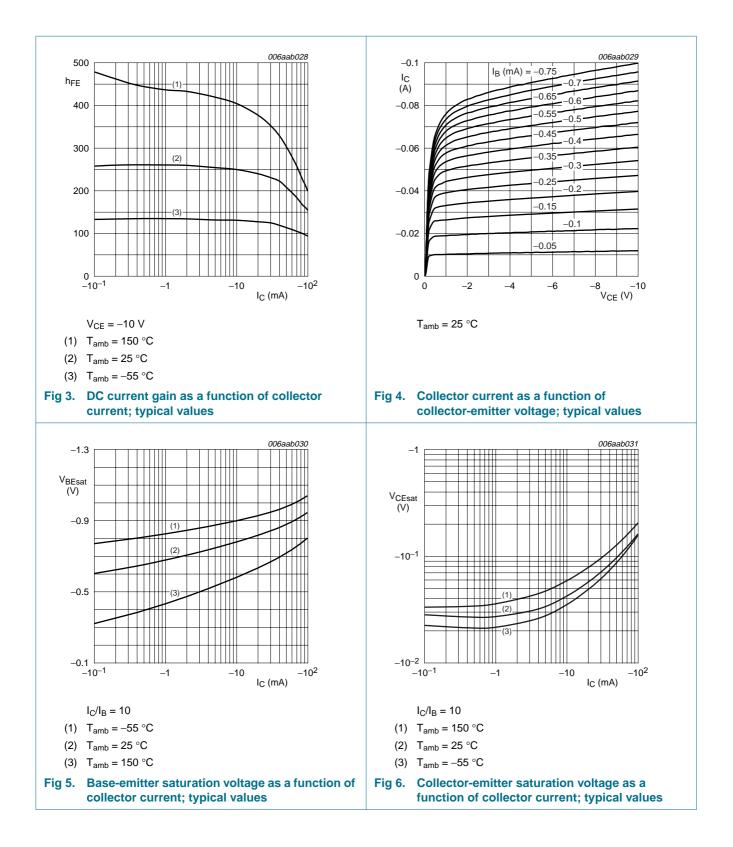
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -45 \text{ V}; \text{ I}_{E} = 0 \text{ A}$		-	-	-10	nA
	current	$V_{CB} = -45 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	-5	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	-10	nA
h _{FE}	DC current gain	$V_{CE} = -10 \text{ V};$ $I_C = -2 \text{ mA}$		210	-	340	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C} = -100 \text{ mA};$ $I_{\rm B} = -10 \text{ mA}$	<u>[1]</u>	-	-	-500	mV
f _T	transition frequency	$V_{CE} = -10 V;$ $I_{C} = -1 mA;$ f = 100 MHz		70	-	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	-	5	pF

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

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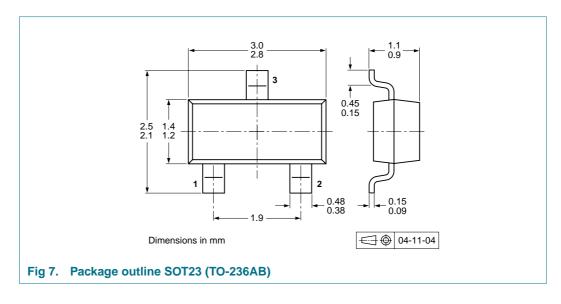
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8. Package outline



9. Packing information

Table 8. Packing methods

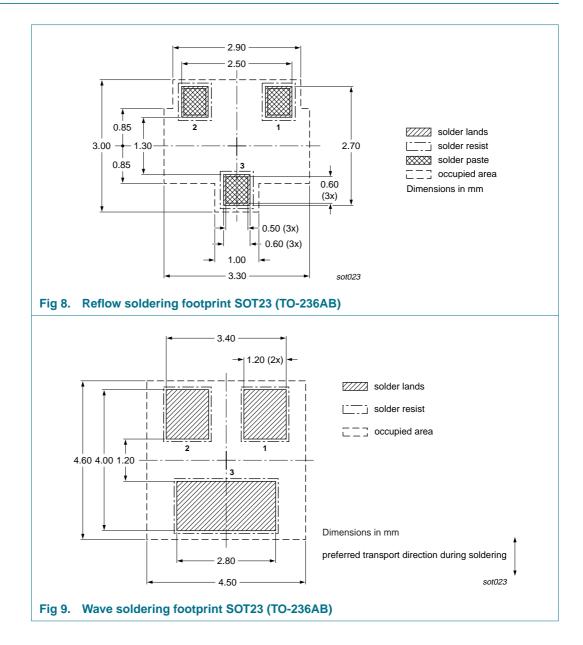
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing qu	Packing quantity	
			3000	10000	
2PB709ART	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235	

[1] For further information and the availability of packing methods, see <u>Section 13</u>.

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10. Soldering



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11. Revision history

Table 9. Revision h	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
2PB709ART_1	20070319	Product data sheet	-	-			

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 19 March 2007 Document identifier: 2PB709ART_1

